

Product Summary

| $V_{(BR)DSS}$ | $R_{DS(on)TYP}$ | I_D |
|---------------|-----------------|-------|
| 60V | 5.5mΩ@10V | 50A |
| | 8.5mΩ@4.5V | |

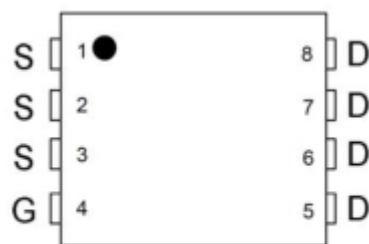
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

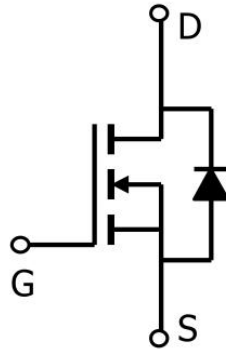
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

Package



PDFNWB3.3×3.3-8L

Circuit diagram



Marking



Absolute maximum ratings

(T_a=25°C unless otherwise noted)

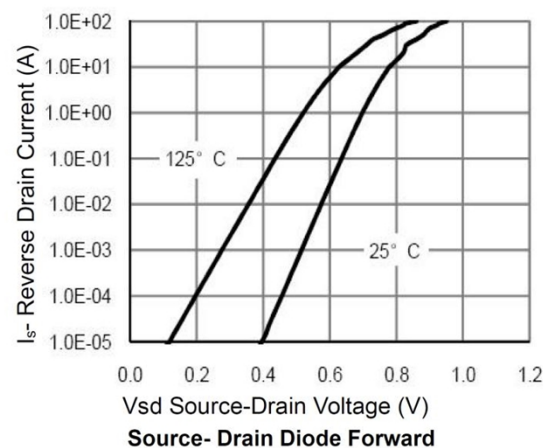
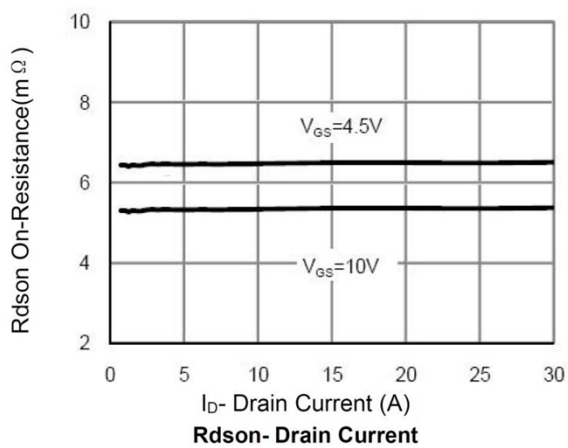
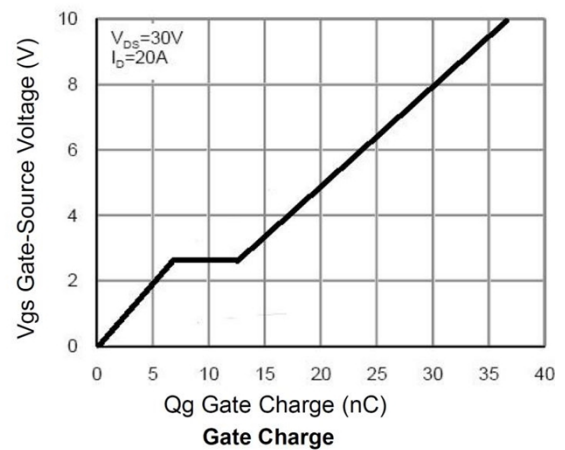
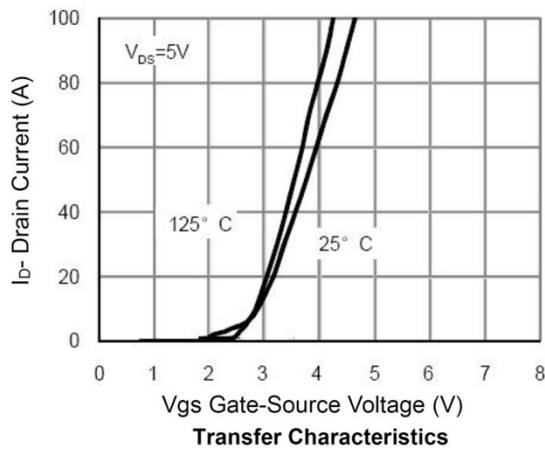
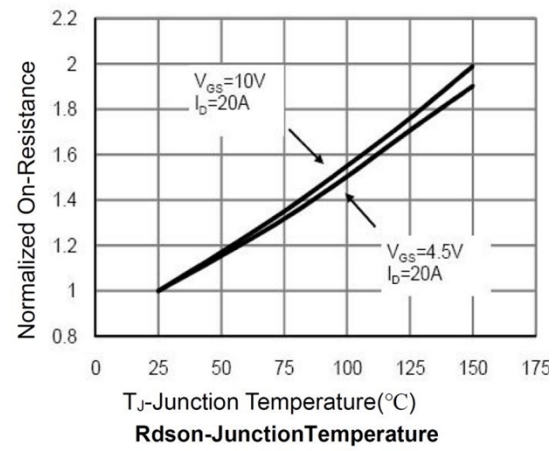
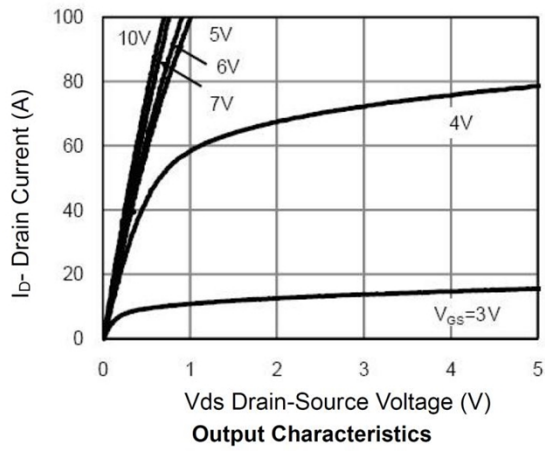
| Parameter | Symbol | Value | Unit |
|-------------------------------------|------------------|-----------|-------|
| Drain-Source Voltage | V _{DS} | 60 | V |
| Gate-Source Voltage | V _{GS} | ±20 | V |
| Continuous Drain Current(Tc=25°C) | I _D | 50 | A |
| Pulse Drain Current Tested | I _{DM} | 200 | A |
| Maximum Power Dissipation(Tc=25°C) | P _D | 31 | W |
| Thermal Resistance-Junction to Case | R _{θJC} | 4.03 | °C/ W |
| Maximum Junction Temperature | T _J | -55~ +150 | °C |
| Storage Temperature Range | T _{STG} | -55~ +150 | °C |

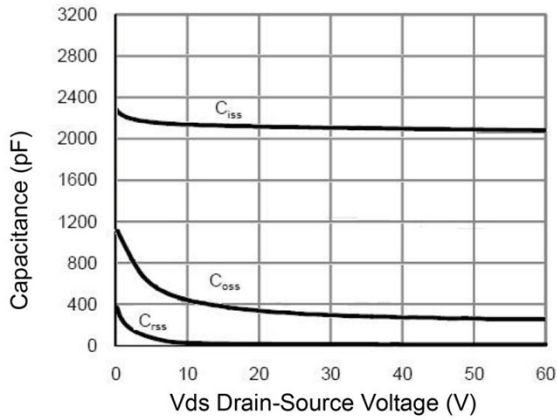
Electrical characteristics

($T_A=25^{\circ}\text{C}$, unless otherwise noted)

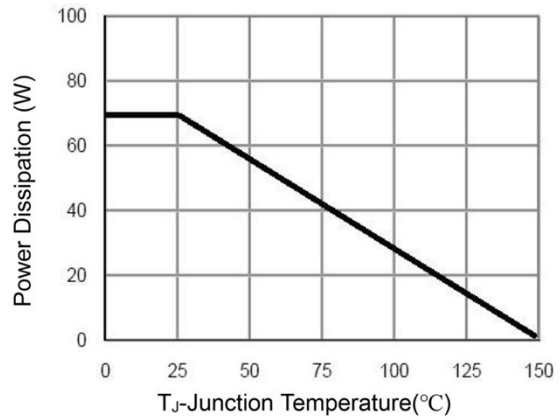
| Parameter | Symbol | Test Condition | Min. | Typ. | Max. | Unit |
|---|---------------------|--|------|------|------|------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV (BR)DSS | V _{GS} = 0V, I _D =250μA | 60 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =48V,V _{GS} = 0V | | | 1 | uA |
| Gate-source leakage current | I _{GSS} | V _{GS} = ±20V,V _{DS} = 0V | | | ±100 | uA |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1 | 2.0 | 3.0 | V |
| Drain-Source On-State Resistance | R _{DS(on)} | V _{GS} =10V, I _D =20A | | 5.5 | 6.9 | mΩ |
| | | V _{GS} =4.5V, I _D =10A | | 8.5 | 11.5 | |
| Dynamic Characteristics Reverse | | | | | | |
| Input Capacitance | C _{iss} | V _{GS} =0V, V _{DS} =30V, f=1MHz | | 2083 | | pF |
| Output Capacitance | C _{oss} | | | 793 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 16 | | |
| Total Gate Charge | Q _g | V _{DS} =30V , V _{GS} =10V, I _D =20A | | 37.5 | | pF |
| Gate-Source Charge | Q _{gs} | | | 6.5 | | |
| Gate-Drain Charge | Q _{gd} | | | 10 | | |
| Turn-On Delay Time | T _{d(on)} | V _{DD} =30V, I _D =20A, V _{GS} =10V, R _G =4.7Ω | | 9 | | nS |
| Rise Time | T _r | | | 3.5 | | |
| Turn-Off Delay Time | T _{d(off)} | | | 32 | | |
| Fall Time | T _f | | | 5.5 | | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Diode Forward Voltage | V _{SD} | V _{GS} =0V ,I _S =1A | | | 1.2 | V |

Typical Characteristics

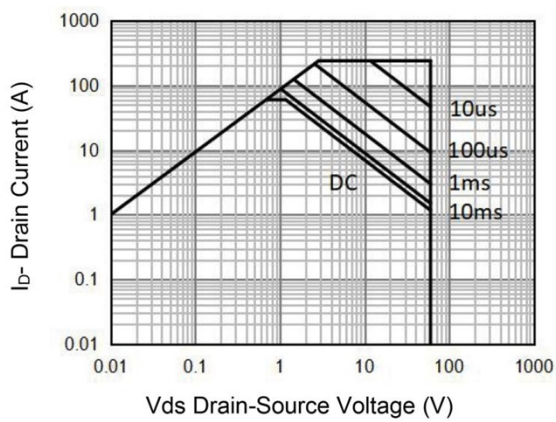




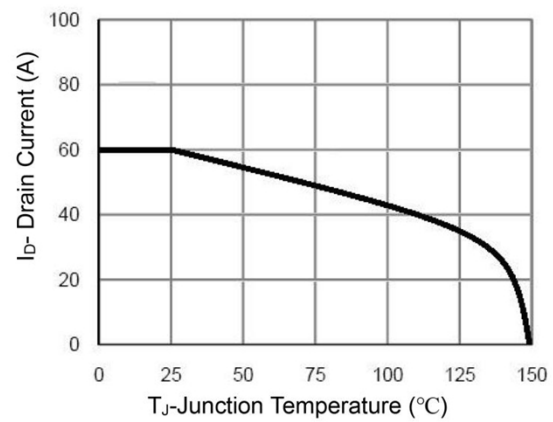
Capacitance vs Vds



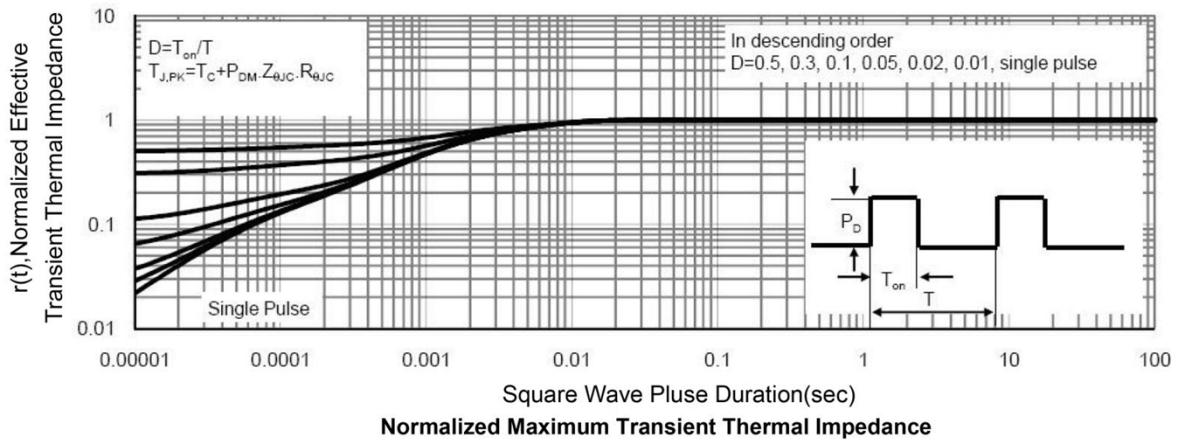
Power De-rating



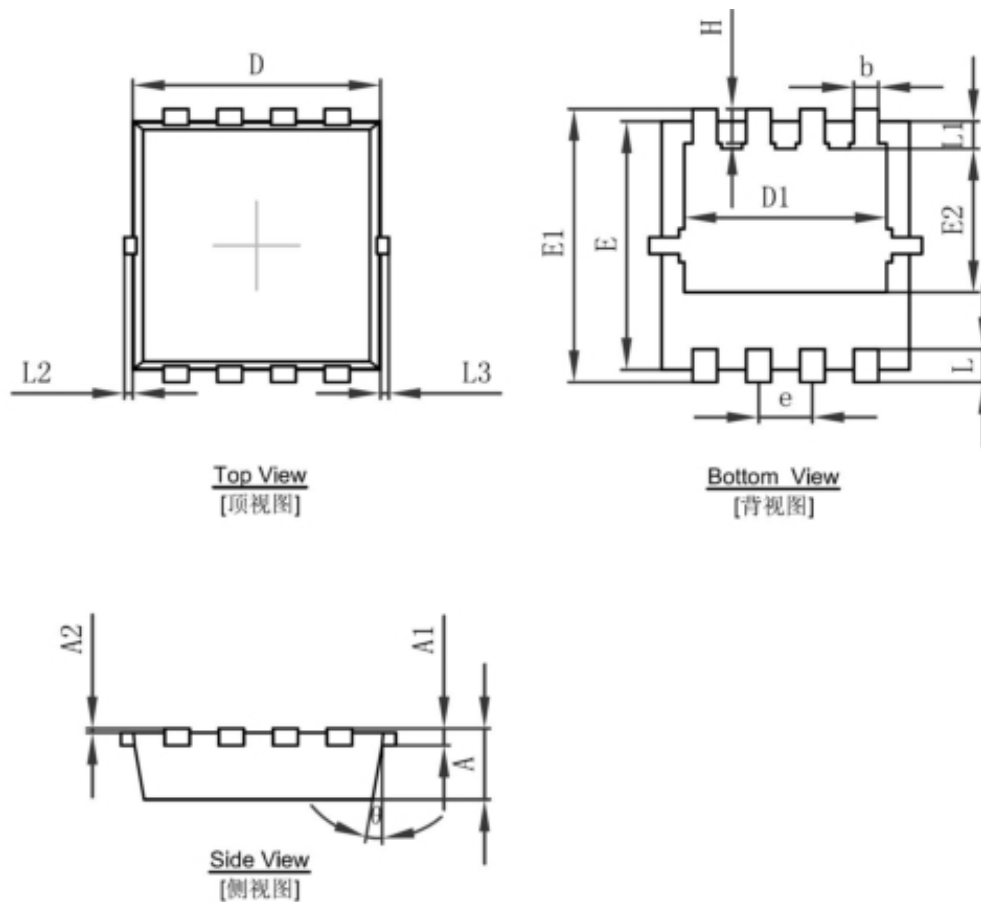
Safe Operation Area



Current De-rating



PDFNWB3.3×3.3-8L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 0.650 | 0.850 | 0.026 | 0.033 |
| A1 | 0.152 REF. | | 0.006 REF. | |
| A2 | 0~0.05 | | 0~0.002 | |
| D | 2.900 | 3.100 | 0.114 | 0.122 |
| D1 | 2.300 | 2.600 | 0.091 | 0.102 |
| E | 2.900 | 3.100 | 0.114 | 0.122 |
| E1 | 3.150 | 3.450 | 0.124 | 0.136 |
| E2 | 1.535 | 1.935 | 0.060 | 0.076 |
| b | 0.200 | 0.400 | 0.008 | 0.016 |
| e | 0.550 | 0.750 | 0.022 | 0.030 |
| L | 0.300 | 0.500 | 0.012 | 0.020 |
| L1 | 0.180 | 0.480 | 0.007 | 0.019 |
| L2 | 0~0.100 | | 0~0.004 | |
| L3 | 0~0.100 | | 0~0.004 | |
| H | 0.315 | 0.515 | 0.012 | 0.020 |
| θ | 9° | 13° | 9° | 13° |